



## MM54HC4078/MM74HC4078 8-Input NOR/OR Gate

### General Description

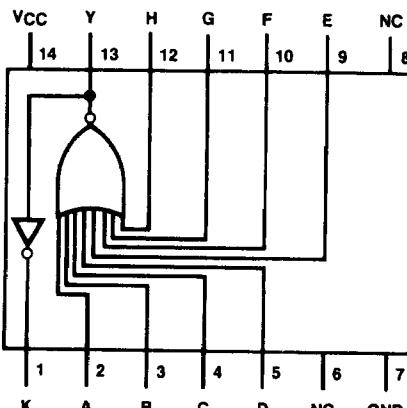
These NOR gates utilize advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits. Both outputs are buffered, providing high noise immunity and the ability to drive 10 LS-TTL loads. The 54HC4078/74HC4078 is functionally equivalent and pin-out compatible with the CD4078B. All inputs are protected from damage due to static discharge by internal diode clamps to V<sub>CC</sub> and ground.

### Features

- Typical propagation delay: 15 ns
- Wide power supply range: 2–6V
- Low quiescent current: 20  $\mu$ A maximum (74HC Series)
- Low input current: 1  $\mu$ A maximum
- Fanout of 10 LS-TTL loads

### Connection and Logic Diagrams

Dual-In-Line Package



TL/F/5135-1

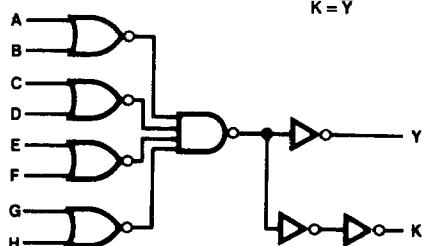
Top View

Order Number MM54HC4078\* or MM74HC4078\*

\*Please look into Section 8, Appendix D for availability of various package types.

$$Y = \overline{A + B + C + D + E + F + G + H}$$

$$K = \overline{Y}$$



TL/F/5135-2

**Absolute Maximum Ratings**

(Notes 1 &amp; 2)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage ( $V_{CC}$ )	-0.5 to + 7.0V
DC Input Voltage ( $V_{IN}$ )	-1.5 to $V_{CC} + 1.5V$
DC Output Voltage ( $V_{OUT}$ )	-0.5 to $V_{CC} + 0.5V$
Clamp Diode Current ( $I_{IK}, I_{OK}$ )	±20 mA
DC Output Current, per pin ( $I_{OUT}$ )	±25 mA
DC $V_{CC}$ or GND Current, per pin ( $I_{CC}$ )	±50 mA
Storage Temperature Range ( $T_{STG}$ )	-65°C to + 150°C
Power Dissipation ( $P_D$ ) (Note 3) S.O. Package only	600 mW 500 mW
Lead Temperature ( $T_L$ ) (Soldering 10 seconds)	260°C

**Operating Conditions**

	Min	Max	Units
Supply Voltage ( $V_{CC}$ )	2	6	V
DC Input or Output Voltage ( $V_{IN}, V_{OUT}$ )	0	$V_{CC}$	V
Operating Temp. Range ( $T_A$ )			
MM74HC	-40	+ 85	°C
MM54HC	-55	+ 125	°C
Input Rise or Fall Times ( $t_r, t_f$ )			
$V_{CC} = 2.0V$	1000	ns	
$V_{CC} = 4.5V$	500	ns	
$V_{CC} = 6.0V$	400	ns	

**DC Electrical Characteristics** (Note 4)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ		$T_A = -40$ to $85^\circ C$	$T_A = -55$ to $125^\circ C$	
$V_{IH}$	Minimum High Level Input Voltage		2.0V	1.5		1.5	1.5	V
			4.5V	3.15		3.15	3.15	V
			6.0V	4.2		4.2	4.2	V
$V_{IL}$	Maximum Low Level Input Voltage**		2.0V	0.5		0.5	0.5	V
			4.5V	1.35		1.35	1.35	V
			6.0V	1.8		1.8	1.8	V
$V_{OH}$	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 20 \mu A$	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 4.0 \text{ mA}$ $ I_{OUT}  \leq 5.2 \text{ mA}$	4.5V	4.2	3.98	3.84	3.7	V
			6.0V	5.7	5.48	5.34	5.2	V
$V_{OL}$	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 20 \mu A$	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 4 \text{ mA}$ $ I_{OUT}  \leq 5.2 \text{ mA}$	4.5V	0.2	0.26	0.33	0.4	V
			6.0V	0.2	0.26	0.33	0.4	V
$I_{IN}$	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		±0.1	±1.0	±1.0	μA
$I_{CC}$	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		2.0	20	40	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: - 12 mW/°C from 65°C to 85°C; ceramic "J" package: - 12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of  $5V \pm 10\%$  the worst case output voltages ( $V_{OH}$  and  $V_{OL}$ ) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case  $V_{IH}$  and  $V_{IL}$  occur at  $V_{CC} = 5.5V$  and 4.5V respectively. (The  $V_{IH}$  value at 5.5V is 3.85V.) The worst case leakage current ( $I_{IN}$ ,  $I_{CC}$ , and  $I_{OZ}$ ) occur for CMOS at the higher voltage and so the 6.0V values should be used.\*\* $V_{IL}$  limits are currently tested at 20% of  $V_{CC}$ . The above  $V_{IL}$  specification (30% of  $V_{CC}$ ) will be implemented no later than Q1, CY'89.

**AC Electrical Characteristics** MM54HC4078/74HC4078 $V_{CC} = 5V$ ,  $T_A = 25^\circ C$ ,  $C_L = 15 \text{ pF}$ ,  $t_r = t_f = 6 \text{ ns}$ 

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Y Output		14	22	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, K Output		16	24	ns

**AC Electrical Characteristics**  $V_{CC} = 2.0V$  to  $6.0V$ ,  $C_L = 50 \text{ pF}$ ,  $t_r = t_f = 6 \text{ ns}$  (unless otherwise specified)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ	Guaranteed Limits			
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Y Output		2.0V	47	130	160	195	ns
			4.5V	17	26	33	39	ns
			6.0V	14	22	28	33	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, K Output		2.0V	50	140	175	210	ns
			4.5V	20	28	35	42	ns
			6.0V	17	24	30	36	ns
$t_{TLH}, t_{THL}$	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	10	15	19	22	ns
			6.0V	9	13	16	19	ns
$C_{PD}$	Power Dissipation Capacitance (Note 5)	(per package)		100				pF
$C_{IN}$	Maximum Input Capacitance			5	10	10	10	pF

Note 5:  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .